

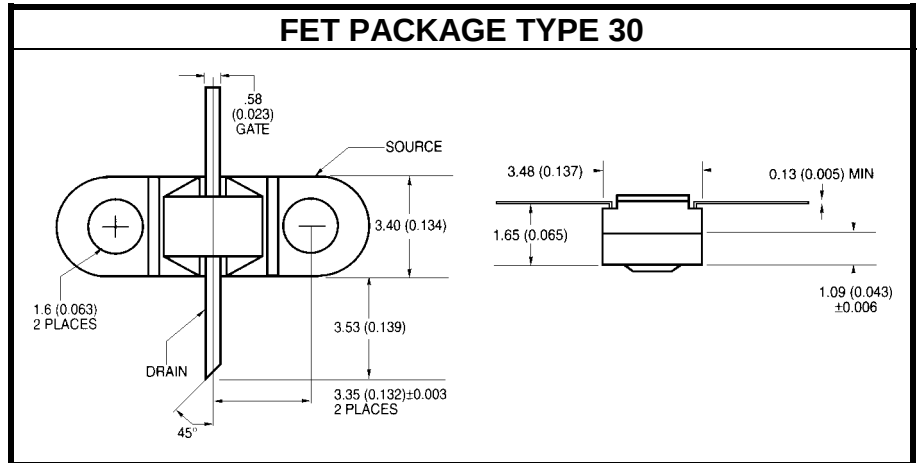
HIGH POWER GaAs FET

FEATURES INCLUDE:

- High Output Power:
P_{1dB} = 1.6 W (TYP) @ 12 GHz
- High power gain:
GLP = 5 dB (TYP) @ 12 GHz
- High power added efficiency:
H_{add} = 18% (TYP) @ 12 GHz

APPLICATIONS:

- S to Ku Band Power Amplifiers



ELECTRICAL SPECIFICATIONS $T_A = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{DDS}	SATURATED DRAIN CURRENT $V_{\text{DS}} = 3.0 \text{ V}$ $V_{\text{GS}} = 0 \text{ V}$	850	1100	1400	mA
$V_{\text{GS (off)}}$	GATE TO SOURCE CUT-OFF VOLTAGE $V_{\text{DS}} = 3.0 \text{ V}$ $I_{\text{D}} = 1.0 \text{ mA}$	-2	-3	-5	V